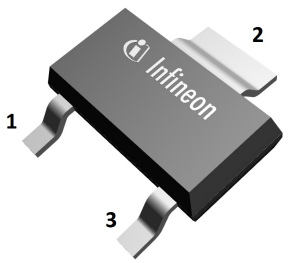
MOSFET

500V CoolMOS™ CE Power Transistor

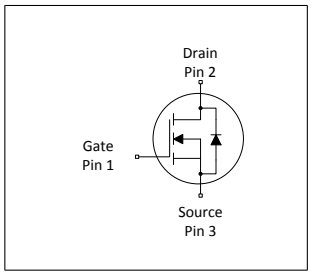
PG-SOT223



CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.

Features

- Extremely low losses due to very low FOM Rdson*Qg and Eoss
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications



Applications

Adapter, Charger and Lighting

Please note: For MOSFET paralleling the use of ferrite beads on the gate or seperate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	550	V
$R_{DS(on),max}$	0.8	Ω
I_D	7.6	A
$Q_{g,typ}$	12.4	nC
$I_{D,pulse}$	15.5	A
E_{oss} @ 400V	1.46	µJ

Type / Ordering Code	Package	Marking	Related Links
IPN50R800CE	PG-SOT223	50S800	see Appendix A

Table of Contents

1 Maximum ratings

at T_j = 25°C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- -	- -	7.6 4.8	A	T_C = 25°C T_C = 100°C
Pulsed drain current[2]	$I_{D,pulse}$	-	-	15.5	A	T_C = 25°C
Avalanche energy, single pulse	E_{AS}	-	-	83	mJ	I_D = 1.9A; V_{DD} = 50V
Avalanche energy, repetitive	E_{AR}	-	-	0.13	mJ	I_D = 1.9A; V_{DD} = 50V
Avalanche current, repetitive	I_{AR}	-	-	1.9	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	V_{DS} = 0...400V
Gate source voltage	V_{GS}	-20 -30	- -	20 30	V	static; AC (f>1 Hz)
Power dissipation	P_{tot}	-	-	5.0	W	T_C = 25°C
Operating and storage temperature	T_j, T_{stg}	-40	-	150	°C	-
Continuous diode forward current	I_S	-	-	1.6	A	T_C = 25°C
Diode pulse current[2]	$I_{S,pulse}$	-	-	15.5	A	T_C = 25°C
Reverse diode dv/dt[3]	dv/dt	-	-	15	V/ns	V_{DS} = 0...400V, I_{SD}<=I_S, T_j=25°C, t_{cond}<2µs
Maximum diode commutation speed[3]	di_f/dt	-	-	500	A/µs	V_{DS} = 0...400V, I_{SD}<=I_S, T_j=25°C, t_{cond}<2µs

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - solder point	R_{thJS}	-	-	23.2	°C/W	-
Thermal resistance, junction - ambient for minimal footprint	R_{thJA}	-	-	160	°C/W	minimal footprint
Thermal resistance, junction - ambient soldered on copper area	R_{thJA}	-	-	75	°C/W	Device on 40mm*40mm*1.5 epoxy PCB FR4 with 6cm² (one layer 70µm thick) copper area for drain connection and cooling. PCB is vertical without blown air.
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	reflow MSL3

[1] DPAK equivalent. Limited by $T_{j\,max}$. Maximum duty cycle D=0.5
[2] Pulse width t_p limited by $T_{j,max}$
[3] V_{DClink}=400V; $V_{DS,peak}$<$V_{(BR)DSS}$; identical low side and high side switch with identical R_G

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	-	-	V	V_{GS}=0V, I_D=1mA
Gate threshold voltage	$V_{GS(th)}$	2.50	3	3.50	V	V_{DS}=V_{GS}, I_D=0.13mA
Zero gate voltage drain current	I_{DSS}	- -	- 10	1 -	µA	V_{DS}=500V, V_{GS}=0V, T_j=25°C V_{DS}=500V, V_{GS}=0V, T_j=150°C
Gate-source leakage curent	I_{GSS}	-	-	100	nA	V_{GS}=20V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	0.72 1.87	0.80 -	Ω	V_{GS}=13V, I_D=1.5A, T_j=25°C V_{GS}=13V, I_D=1.5A, T_j=150°C
Gate resistance	R_G	-	3	-	Ω	f=1 MHz, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	280	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output capacitance	C_{oss}	-	23	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Effective output capacitance, energy related[1)]	$C_{o(er)}$	-	18	-	pF	V_{GS}=0V, V_{DS}=0...400V
Effective output capacitance, time related[2)]	$C_{o(tr)}$	-	67	-	pF	I_D=constant, V_{GS}=0V, V_{DS}=0...400V
Turn-on delay time	$t_{d(on)}$	-	6.2	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.9A, R_G=5.3Ω
Rise time	t_r	-	5.5	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.9A, R_G=5.3Ω
Turn-off delay time	$t_{d(off)}$	-	26	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.9A, R_G=5.3Ω
Fall time	t_f	-	15.9	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.9A, R_G=5.3Ω

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	1.5	-	nC	V_{DD}=400V, I_D=1.9A, V_{GS}=0 to 10V
Gate to drain charge	Q_{gd}	-	6.8	-	nC	V_{DD}=400V, I_D=1.9A, V_{GS}=0 to 10V
Gate charge total	Q_g	-	12.4	-	nC	V_{DD}=400V, I_D=1.9A, V_{GS}=0 to 10V
Gate plateau voltage	$V_{plateau}$	-	5.3	-	V	V_{DD}=400V, I_D=1.9A, V_{GS}=0 to 10V

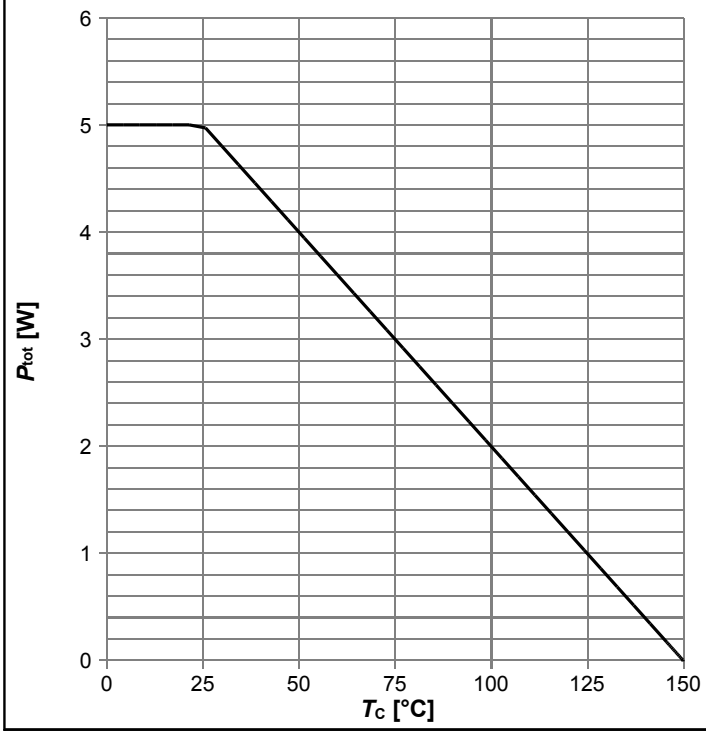
[1)] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V
[2)] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.83	-	V	V_{GS}=0V, I_F=1.9A, T_f=25°C
Reverse recovery time	t_{rr}	-	158	-	ns	V_R=400V, I_F=1.9A, di_F/dt=100A/µs
Reverse recovery charge	Q_{rr}	-	0.84	-	µC	V_R=400V, I_F=1.9A, di_F/dt=100A/µs
Peak reverse recovery current	I_{rrm}	-	9.6	-	A	V_R=400V, I_F=1.9A, di_F/dt=100A/µs

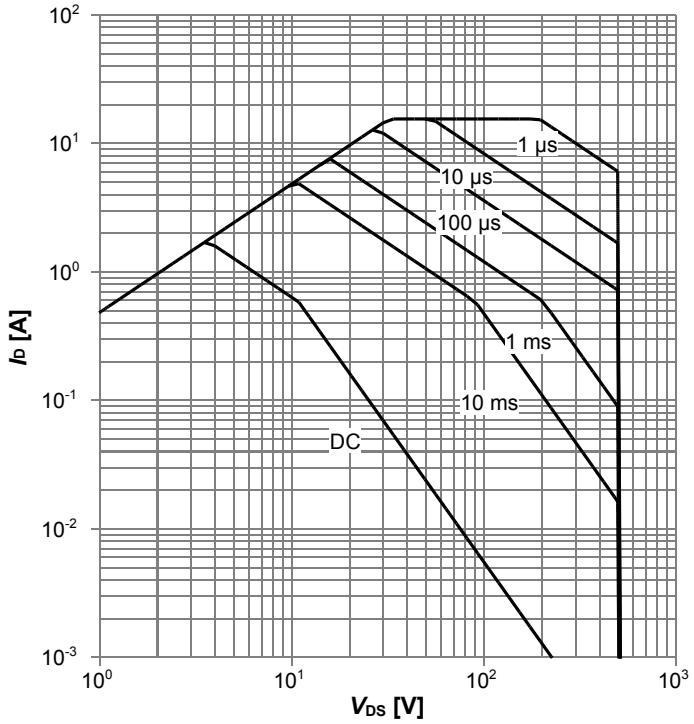
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



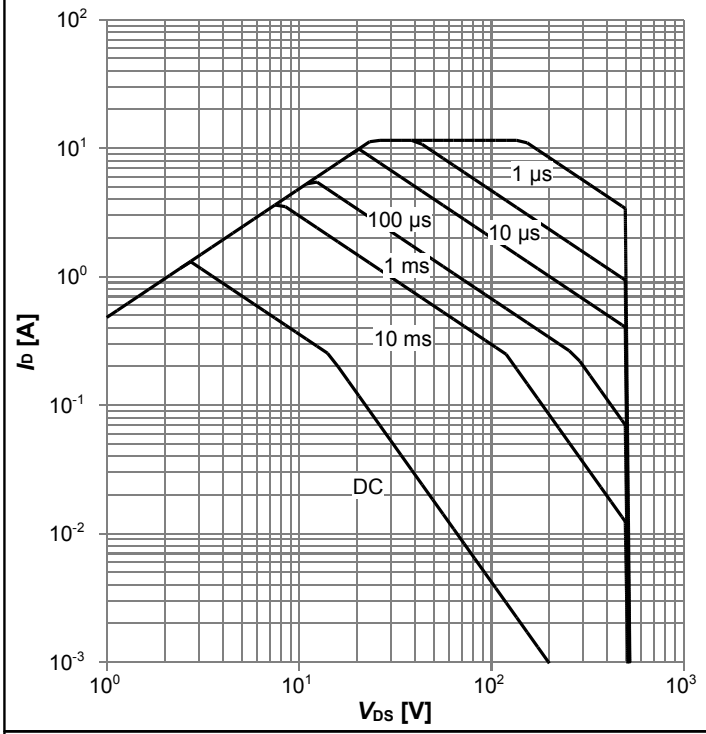
$P_{tot}=f(T_C)$

Diagram 2: Safe operating area



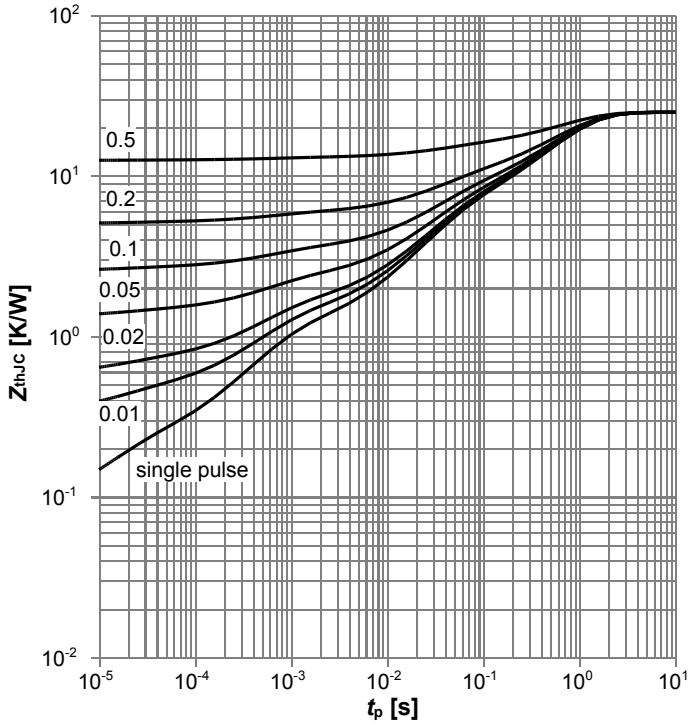
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 3: Safe operating area



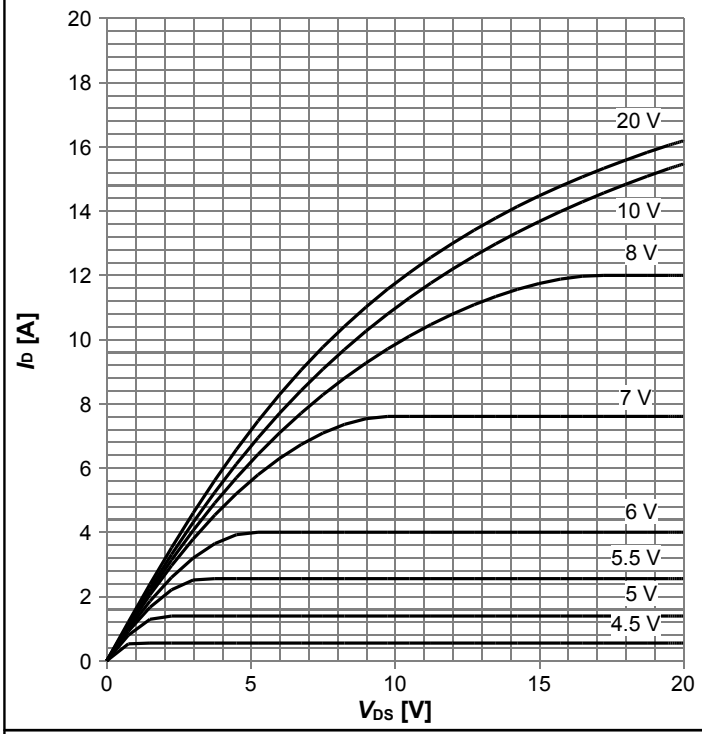
$I_D=f(V_{DS})$; $T_C=80$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



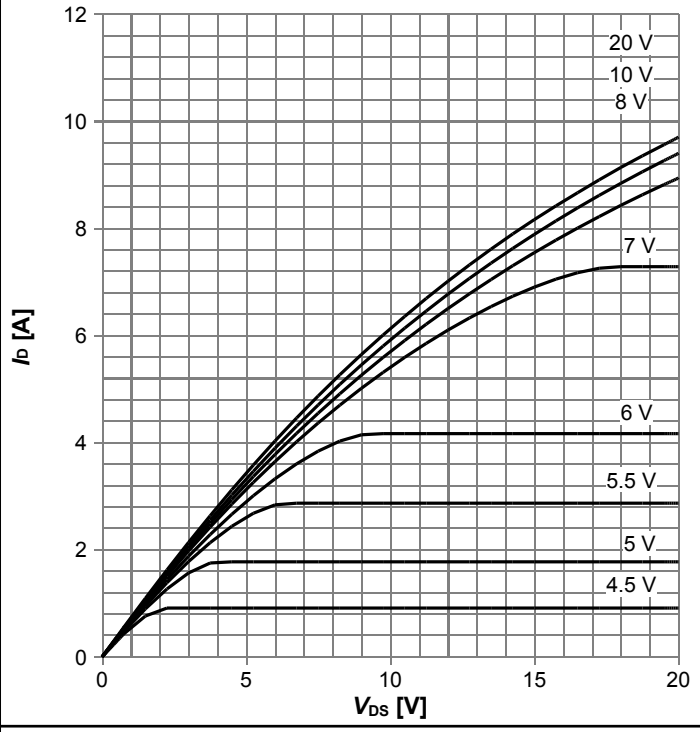
$Z_{thJC}=f(t_P)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



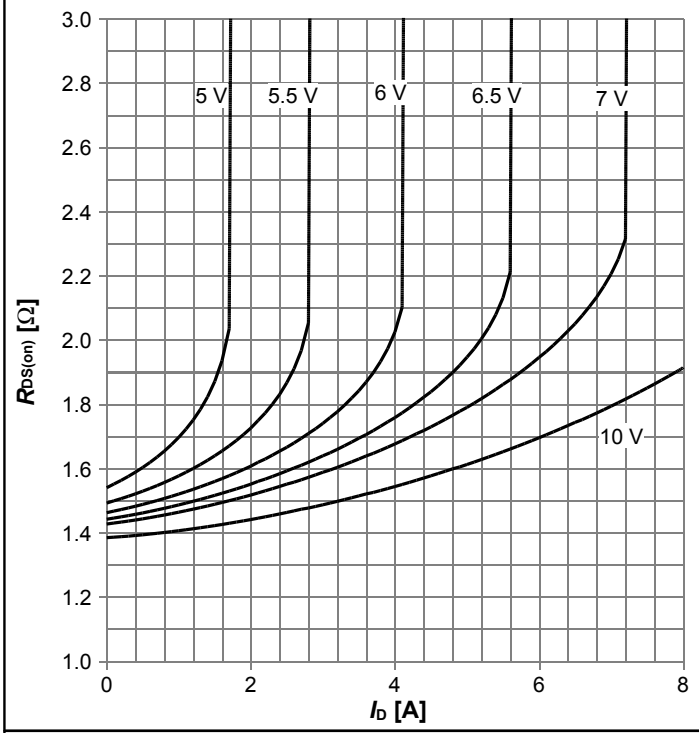
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. output characteristics



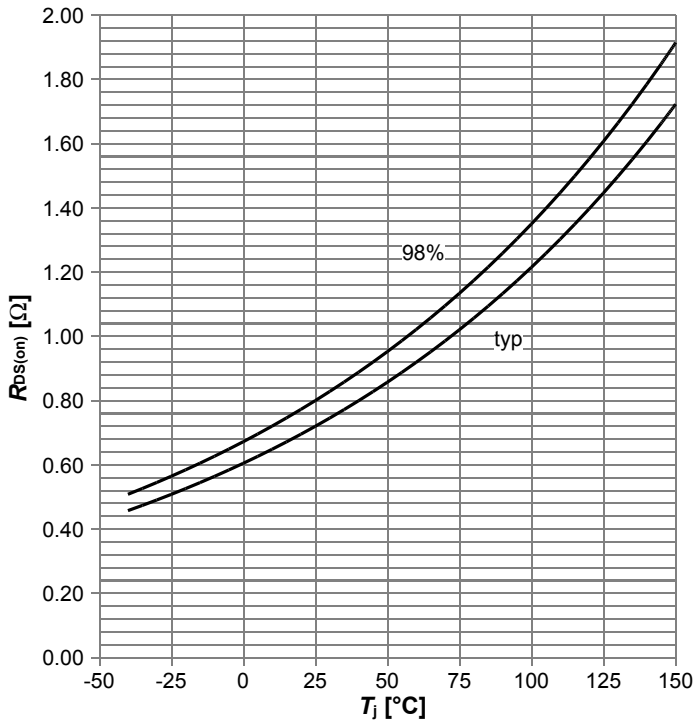
I_D=f(V_{DS}); T_j=125 °C; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



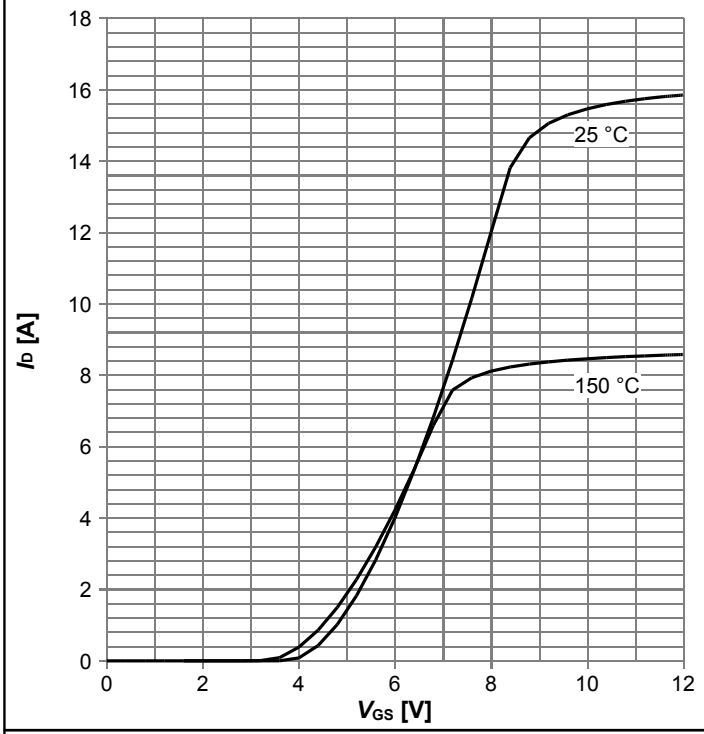
$R_{DS(on)}$=f(I_D); T_j=125 °C; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



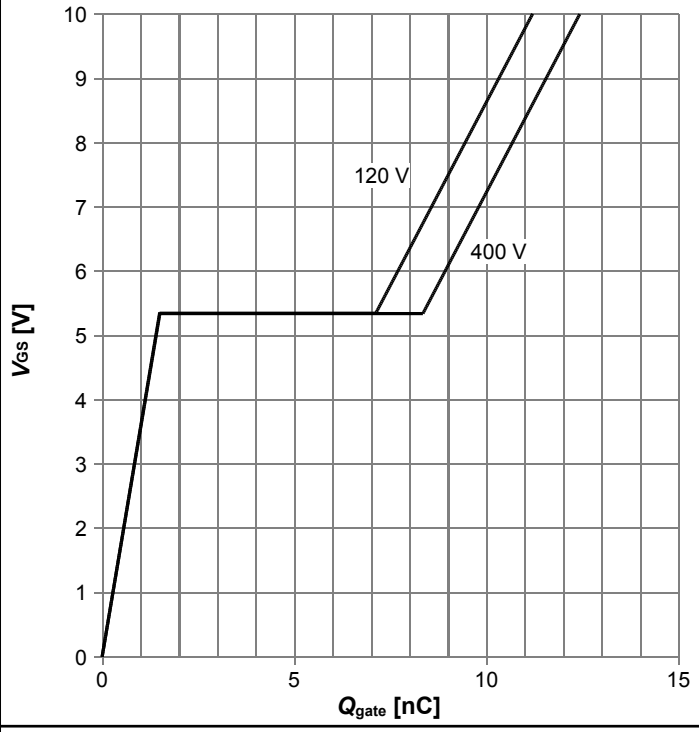
$R_{DS(on)}$=f(T_j); I_D=1.5 A; V_{GS}=13 V

Diagram 9: Typ. transfer characteristics



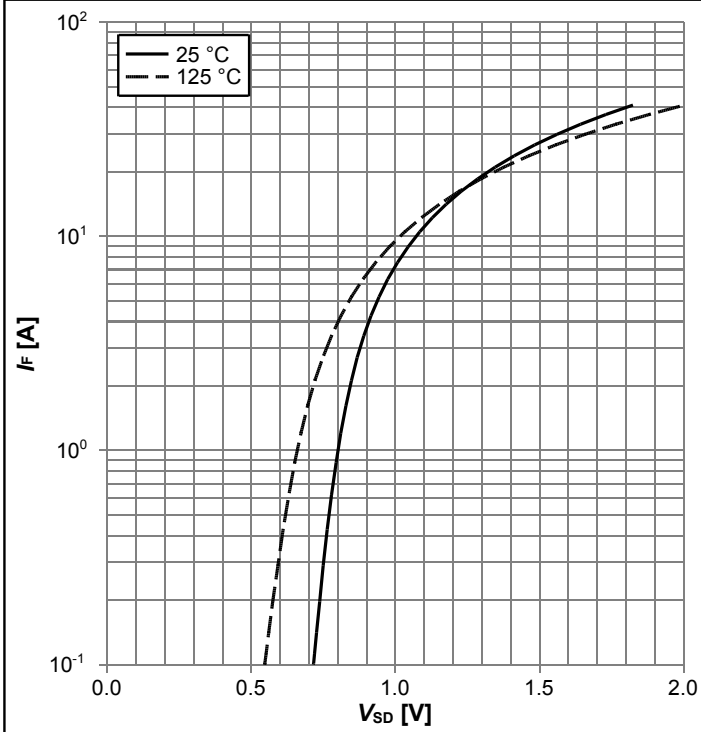
I_D=f(V_{GS}); V_{DS}=20V; parameter: T_j

Diagram 10: Typ. gate charge



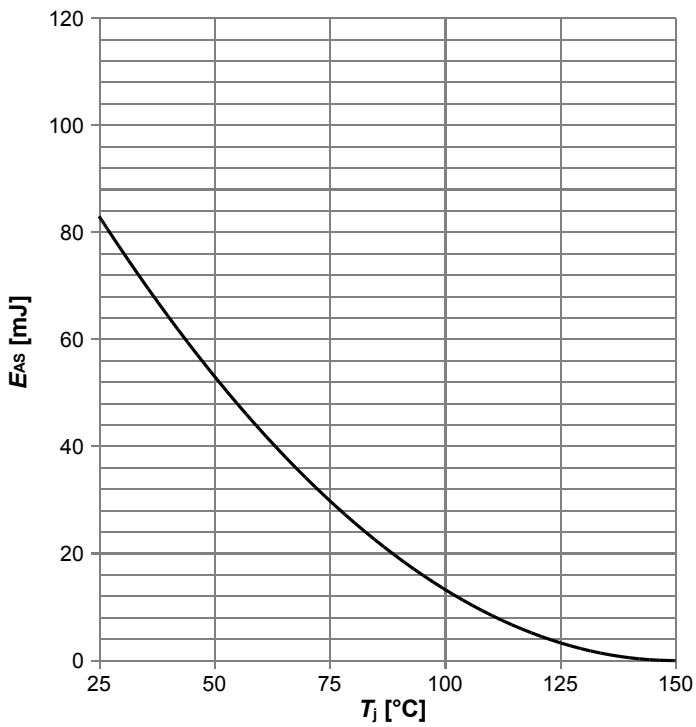
V_{GS}=f(Q_{gate}); I_D=1.9 A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



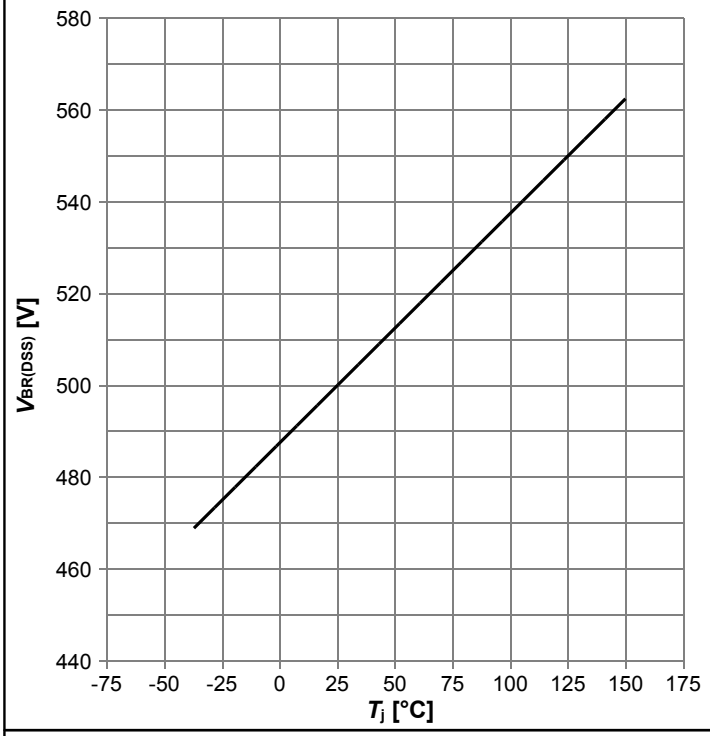
I_F=f(V_{SD}); parameter: T_j

Diagram 12: Avalanche energy



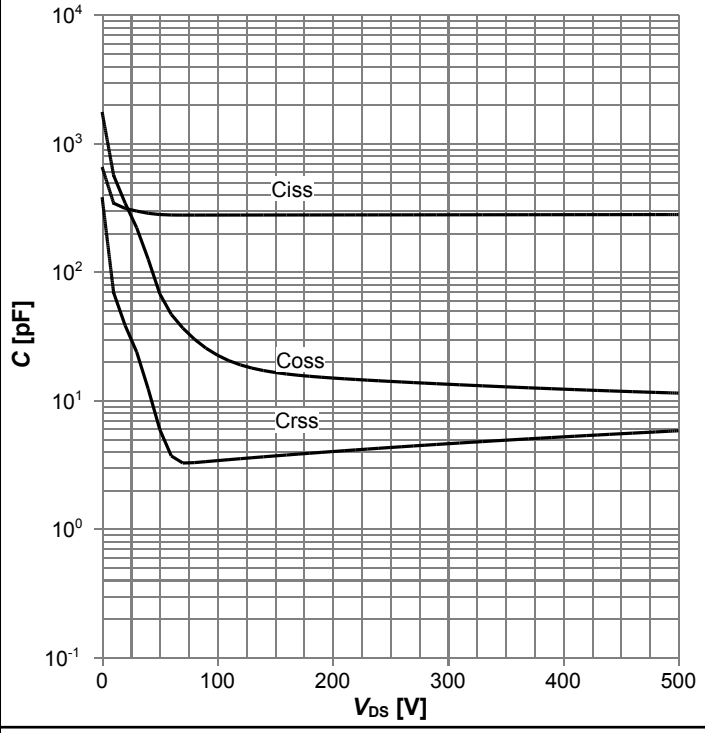
E_{AS}=f(T_j); I_D=1.9 A; V_{DD}=50 V

Diagram 13: Drain-source breakdown voltage



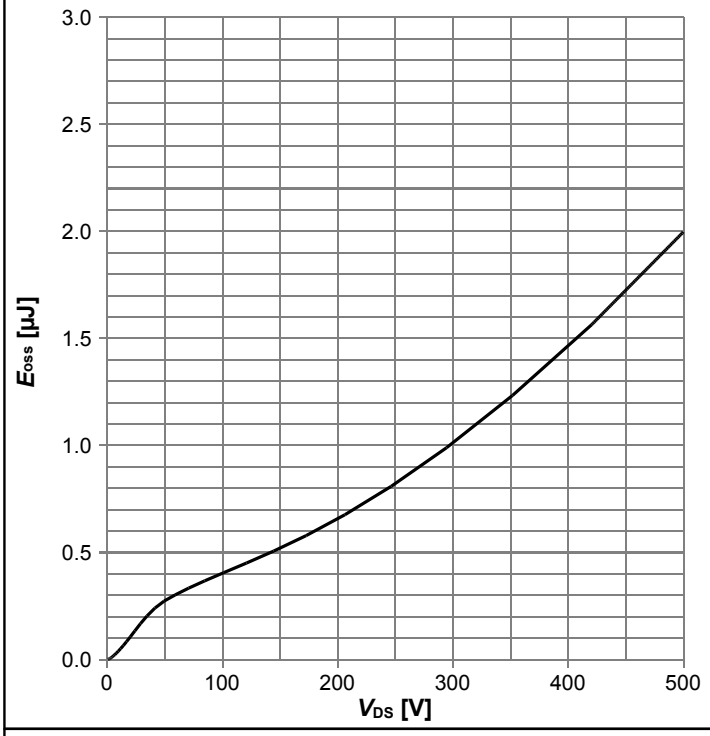
$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Diagram 14: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 15: Typ. Coss stored energy



E_{oss}=f(V_{DS})

5 Test Circuits

Table 8 Diode characteristics

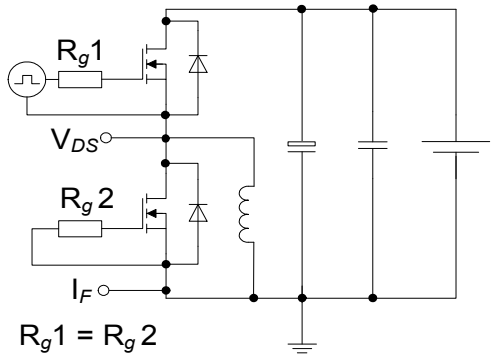
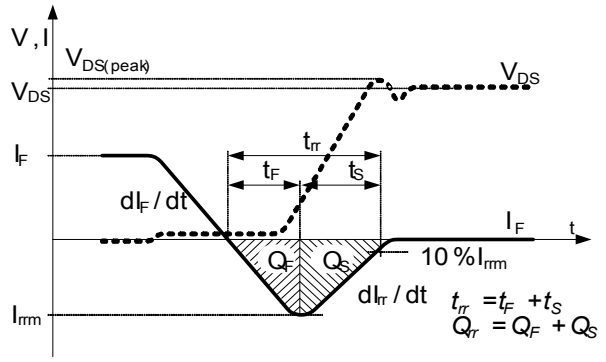
Test circuit for diode characteristics	Diode recovery waveform
	

Table 9 Switching times

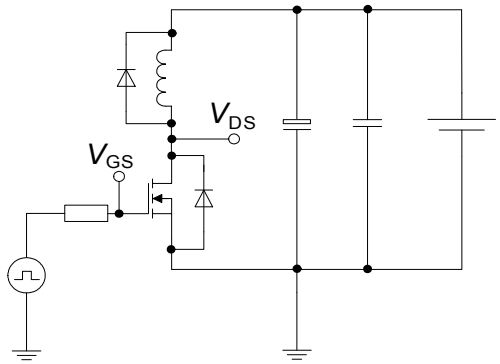
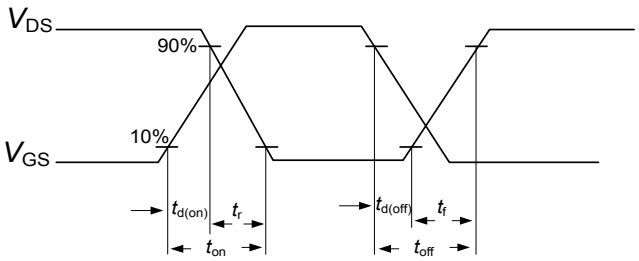
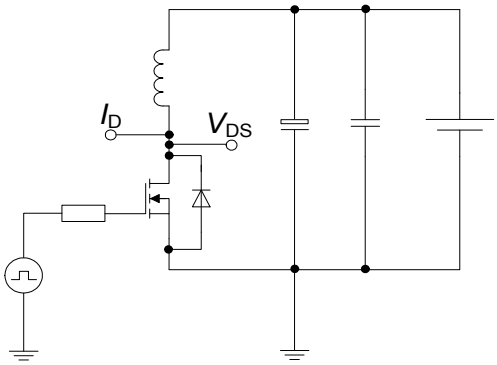
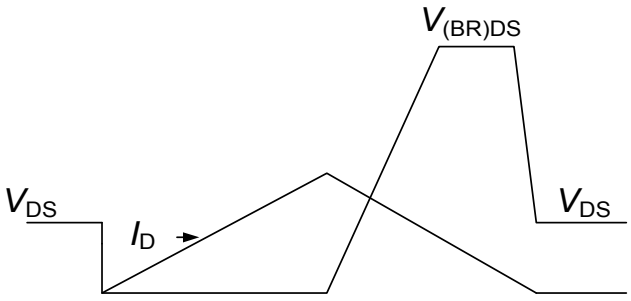
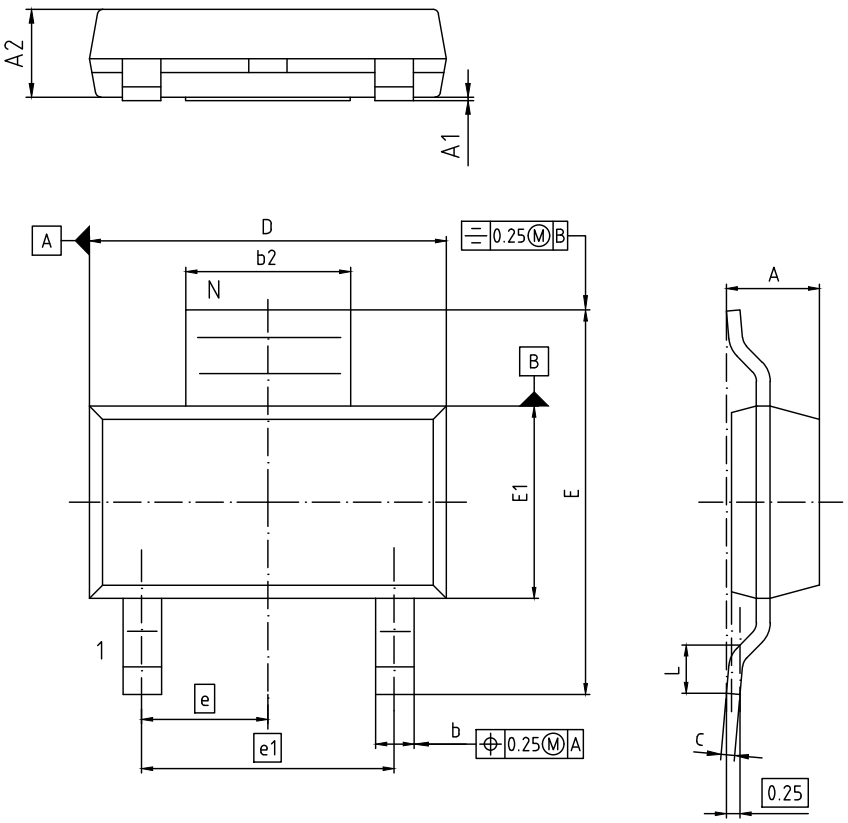
Switching times test circuit for inductive load	Switching times waveform
	

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

6 Package Outlines



NOTES:

1. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-261

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.52	1.80	0.060	0.071
A1	-	0.10	-	0.004
A2	1,50	1.70	0.059	0.067
b	0.60	0.80	0.024	0.031
b2	2.95	3.10	0.116	0.122
c	0.24	0.32	0.009	0.013
D	6.30	6.70	0.248	0.264
E	6.70	7.30	0.264	0.287
E1	3.30	3.70	0.130	0.146
e	2.3 BASIC		0.091 BASIC	
e1	4.6 BASIC		0.181 BASIC	
L	0.75	1.10	0.030	0.043
N	3		3	
O	0°	10°	0°	10°

DOCUMENT NO.
Z8B00180553

SCALE
0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
24-02-2016

REVISION
01

Figure 1 Outline PG-SOT223, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- **IFX CoolMOS Webpage:** www.infineon.com
- **IFX Design tools:** www.infineon.com

Revision History

IPN50R800CE

Revision: 2016-06-13, Rev. 2.1

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2016-04-29	Release of final version
2.1	2016-06-13	Updated ID ratings

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Published by
Infineon Technologies AG
81726 München, Germany

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